AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (currently amended): A self-supported nitride semiconductor substrate having an X-ray diffraction half width of ~~278~~ 50 seconds or less in a {20-24} diffraction plane, a diameter of 10 mm or more and a thickness of 200 μm or more~~, wherein a base seed substrate used for growing said self-supported nitride semiconductor substrate thereon is made of a different material from that of said self-supported substrate~~.

2. (original): The self-supported nitride semiconductor substrate according to claim 1, wherein said nitride semiconductor is undoped, or n- or p-type, and has a carrier density of 1 x 10^{20} cm^{-3} or less.

3. (currently amended/withdrawn): A method for producing a self-supported nitride semiconductor substrate having an X-ray diffraction half width of 500 seconds or less in at least one of a {20-24} diffraction plane and a {11-24} diffraction plane, and a diameter of 10 mm or more, said method comprising (1) forming a first nitride semiconductor layer having a dislocation density of $10^n/cm^2$ ($0 < n \leq 10$) on a base substrate; (2) forming a mask layer made of another material than said nitride semiconductor on said first nitride semiconductor layer; (3) providing said mask layer with openings having an area of 10^{-n} cm^2 or less, which penetrate said mask layer in a thickness direction, at a density of $10^{n-2}/cm^2$ or less; (4) forming a second nitride

semiconductor layer having a thickness of 50 μm or more on said mask layer; and (5) removing layers ranging from said base substrate to said mask layer.

4. (withdrawn): The method for producing a self-supported nitride semiconductor substrate according to claim 3, wherein said openings were at a density of $10^{n-4}/cm^2$ or less in said mask layer.

5. (withdrawn): The method for producing a self-supported nitride semiconductor substrate according to 3, wherein the growing of said nitride semiconductor is carried out by a sublimation method, a metal-organic vapor phase epitaxy method, a hydride vapor-phase epitaxy method, liquid-phase epitaxy method or a combination thereof.

6. (withdrawn): The method for producing a self-supported nitride semiconductor substrate according to claim 3, wherein said base substrate is made of a different material from that of said self-supported substrate.

7. (withdrawn): The method for producing a self-supported nitride semiconductor substrate according to claim 3, wherein said first nitride semiconductor layer is formed on said base substrate via a buffer layer.

8. (currently amended): A light-emitting nitride semiconductor device comprising an epitaxial nitride layer with a light-emitting device structure formed on a self-supported nitride semiconductor substrate having an X-ray diffraction half width of ~~278~~ 50 seconds or less in a

{20-24} diffraction plane, a diameter of 10 mm or more and a thickness of 200 μm or more~~, wherein a base seed substrate used for growing said self-supported nitride semiconductor substrate thereon is made of a different material from that of said self-supported substrate~~.